

50 V, 500 mA NPN/PNP Resistor-Equipped double Transistor (RET); R1 = 2.2 k $\Omega$ , R2 = 10 k $\Omega$ 

**16 February 2022** 

**Product data sheet** 

## 1. General description

NPN/PNP Resistor-Equipped double Transistor (RET) in a small SOT457 (SC-74) Surface-Mounted Device (SMD) plastic package.

NPN/NPN complement: PIMN32-Q PNP/PNP complement: PIMP32-Q

### 2. Features and benefits

- 500 mA output current capability
- Built-in bias resistors
- Simplifies circuit design
- · Reduces component count
- Reduces pick and place costs
- Qualified according to AEC-Q101 and recommended for use in automotive applications

## 3. Applications

- · Digital applications
- Cost-saving alternative to BC807-Q / BC817-Q series in digital applications
- · Control of IC inputs
- Switching loads

## 4. Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
Per transistor;	Per transistor; for the PNP transistor (TR2) with negative polarity where applicable							
V <sub>CEO</sub>	collector-emitter voltage	open base		-	-	50	V	
Io	output current			-	-	500	mA	
R1	bias resistor 1 (input)		[1]	1.54	2.2	2.86	kΩ	
R2/R1	bias resistor ratio		[1]	4.1	4.55	5		

[1] See section "Test information" for resistor calculation and test conditions.



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# 5. Pinning information

**Table 2. Pinning information** 

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	GND1	GND (emitter) TR1		O1 I2 GND2
2	I1	input (base) TR1		
3	O2	output (collector) TR2	<u> </u>	R1 R2
4	GND2	GND (emitter) TR2		TR2
5	12	input (base) TR2	<u>                                     </u>	TR1 R2 R2
6	O1	output (collector) TR1	SC-74; TSOP6 (SOT457)	GND1 I1 O2
				aaa-007379

# 6. Ordering information

**Table 3. Ordering information** 

Type number Package					
	Name	Description	Version		
PIMC32-Q	SC-74; TSOP6	plastic, surface-mounted package (SC-74; TSOP6); 6 leads	SOT457		

# 7. Marking

## Table 4. Marking codes

Type number	Marking code
PIMC32-Q	4н

# 8. Limiting values

### **Table 5. Limiting values**

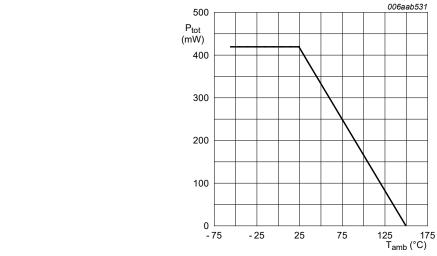
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transist	or; for the PNP transistor (TR	22) with negative polarity where applicable	е		•	
V <sub>CBO</sub>	collector-base voltage	open emitter		-	50	V
V <sub>CEO</sub>	collector-emitter voltage	open base		-	50	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	5	V
VI	input voltage			-5	12	V
Io	output current			-	500	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	290	mW
Per device	·		•			
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	420	mW
Tj	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided, 35 µm copper, tin-plated and standard footprint.

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FR4 PCB, single-sided, 35 µm copper, tin-plated and standard footprint

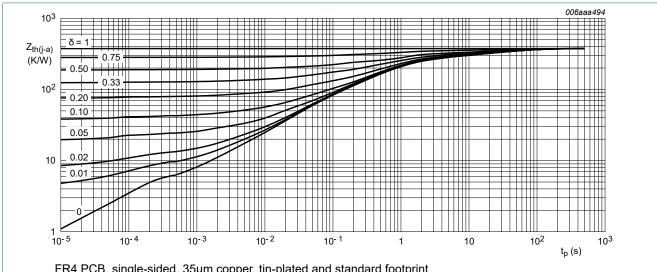
Fig. 1. Per device: Power derating curve

## 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor							
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	432	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	-	105	K/W
Per device							
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	298	K/W

[1] Device mounted on an FR4 PCB, single-sided, 35 µm copper, tin-plated and standard footprint.



FR4 PCB, single-sided, 35µm copper, tin-plated and standard footprint

Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; Fig. 2. typical values

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## 10. Characteristics

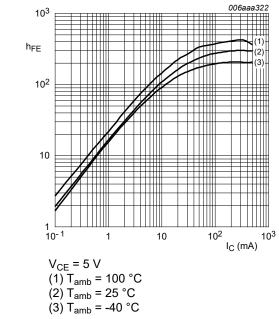
#### **Table 7. Characteristics**

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transist	or; for the PNP transistor (	TR2) with negative polarity where appl	icable	'			
V <sub>(BR)CBO</sub>	collector-base breakdown voltage	$I_C = 100 \ \mu A; I_E = 0 \ A; T_{amb} = 25 \ ^{\circ}C$		50	-	-	V
$V_{(BR)CEO}$	collector-emitter breakdown voltage	$I_C = 10 \text{ mA}; I_B = 0 \text{ A}; T_{amb} = 25 \text{ °C}$		50	-	-	V
I <sub>CBO</sub>	collector-base cut-off current	V <sub>CB</sub> = 50 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C		-	-	100	nA
I <sub>CEO</sub>	collector-emitter cut-off current	V <sub>CE</sub> = 50 V; I <sub>B</sub> = 0 A; T <sub>amb</sub> = 25 °C		-	-	0.5	μΑ
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$		-	-	0.65	mA
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = 5 V; I <sub>C</sub> = 50 mA; T <sub>amb</sub> = 25 °C		70	-	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C = 50 \text{ mA}; I_B = 2.5 \text{ mA}; T_{amb} = 25 ^{\circ}\text{C}$		-	-	100	mV
V <sub>I(off)</sub>	off-state input voltage	V <sub>CE</sub> = 5 V; I <sub>C</sub> = 100 μA; T <sub>amb</sub> = 25 °C		0.4	0.65	1	V
V <sub>I(on)</sub>	on-state input voltage	V <sub>CE</sub> = 0.3 V; I <sub>C</sub> = 20 mA; T <sub>amb</sub> = 25 °C		0.5	0.95	1.4	V
R1	bias resistor 1 (input)		[1]	1.54	2.2	2.86	kΩ
R2/R1	bias resistor ratio		[1]	4.1	4.55	5	
TR1 (NPN)					·	·	
C <sub>c</sub>	collector capacitance	$V_{CB}$ = 10 V; $I_{E}$ = 0 A; $i_{e}$ = 0 A; f = 1 MHz; $T_{amb}$ = 25 °C		-	7	-	pF
f <sub>T</sub>	transition frequency	$V_{CE}$ = 5 V; $I_{C}$ = 50 mA; f = 100 MHz; $T_{amb}$ = 25 °C	[2]	-	225	-	MHz
TR2 (PNP)							
C <sub>c</sub>	collector capacitance	$V_{CB}$ = -10 V; $I_{E}$ = 0 A; $i_{e}$ = 0 A; $f$ = 1 MHz; $T_{amb}$ = 25 °C		-	11	-	pF
f <sub>T</sub>	transition frequency	$V_{CE}$ = -5 V; $I_{C}$ = -50 mA; f = 100 MHz; $T_{amb}$ = 25 °C	[2]	-	140	-	MHz

<sup>[1]</sup> See section "Test information" for resistor calculation and test conditions.

<sup>[2]</sup> Characteristics of built-in transistor

## 50 V, 500 mA NPN/PNP Resistor-Equipped double Transistor (RET); R1 = 2.2 k $\Omega$ , R2 = 10 k $\Omega$



TR1 (NPN): DC current gain as a function of Fig. 3. collector current; typical values

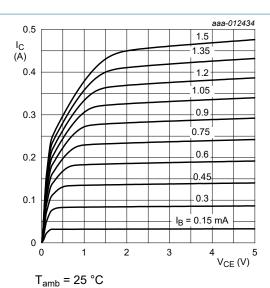
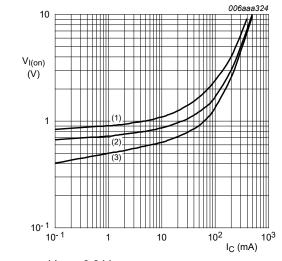


Fig. 4. TR1 (NPN): Collector current as a function of collector-emitter voltage; typical values



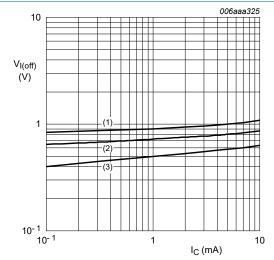
 $V_{CE}$  = 0.3 V

(1)  $T_{amb}$  = -40 °C

(2)  $T_{amb} = 25 \, ^{\circ}C$ 

(3)  $T_{amb} = 100 \, ^{\circ}C$ 

Fig. 5. TR1 (NPN): On-state input voltage as a function | Fig. 6. of collector current; typical values



 $V_{CE} = 5 V$ 

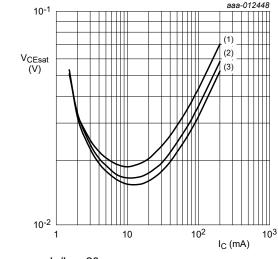
(1)  $T_{amb}$  = -40 °C

(2)  $T_{amb} = 25 \, ^{\circ}C$ 

(3)  $T_{amb} = 100 \, ^{\circ}C$ 

TR1 (NPN): Off-state input voltage as a function of collector current; typical values

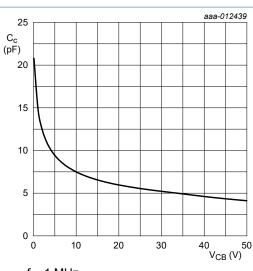
## 50 V, 500 mA NPN/PNP Resistor-Equipped double Transistor (RET); R1 = 2.2 k $\Omega$ , R2 = 10 k $\Omega$



 $I_{\rm C}/I_{\rm B} = 20$ 

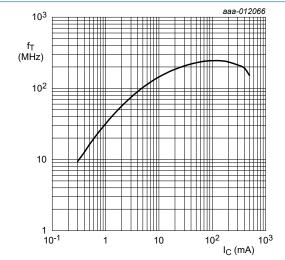
(1) T<sub>amb</sub> = 100 °C (2) T<sub>amb</sub> = 25 °C (3) T<sub>amb</sub> = -40 °C

Fig. 7. TR1 (NPN): Collector-emitter saturation voltage as a function of collector current; typical values



f = 1 MHz $T_{amb}$  = 25 °C

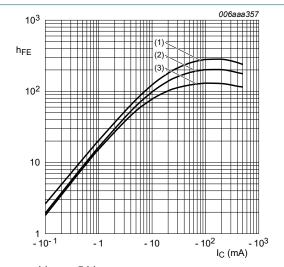
Fig. 8. TR1 (NPN): Collector capacitance as a function of collector-base voltage; typical values



f = 100 MHz  $T_{amb} = 25 \, ^{\circ}C$ 

 $V_{CE} = 5 V$ 

Fig. 9. TR1 (NPN): Transition frequency as a function of collector current; typical values of built-in transistor



 $V_{CE}$  = -5 V

(1)  $T_{amb} = 100 \, ^{\circ}C$ 

(2)  $T_{amb} = 25 \, ^{\circ}C$ 

(3)  $T_{amb} = -40 \, ^{\circ}C$ 

Fig. 10. TR2 (PNP): DC current gain as a function of collector current; typical values

## 50 V, 500 mA NPN/PNP Resistor-Equipped double Transistor (RET); R1 = 2.2 k $\Omega$ , R2 = 10 k $\Omega$

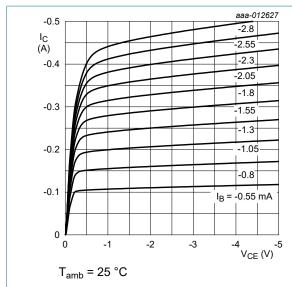
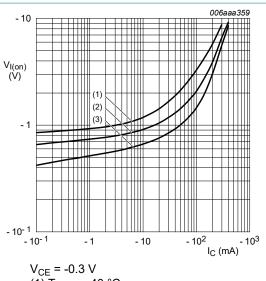
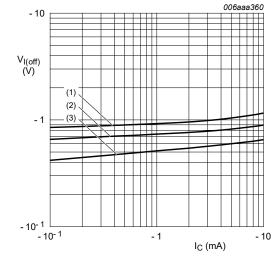


Fig. 11. TR2 (PNP): Collector current as a function of collector-emitter voltage, typical values



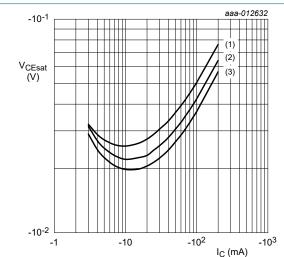
V<sub>CE</sub> = -0.3 V (1) T<sub>amb</sub> = -40 °C (2) T<sub>amb</sub> = 25 °C (3)  $T_{amb} = 100 \, ^{\circ}C$ 

Fig. 12. TR2 (PNP): On-state input voltage as a function of collector current; typical values



 $V_{CE} = -5 V$ (1)  $T_{amb} = -40 \, ^{\circ}C$ (2) T<sub>amb</sub> = 25 °C (3) T<sub>amb</sub> = 100 °C

Fig. 13. TR2 (PNP): Off-state input voltage as a function | Fig. 14. TR2 (PNP): Collector-emitter saturation voltage of collector current; typical values



 $I_{\rm C}/I_{\rm B} = 20$ (1) T<sub>amb</sub> = 100 °C (2)  $T_{amb} = 25 \, ^{\circ}C$ (3)  $T_{amb} = -40 \, ^{\circ}C$ 

as a function of collector current; typical values

## 50 V, 500 mA NPN/PNP Resistor-Equipped double Transistor (RET); R1 = 2.2 k $\Omega$ , R2 = 10 k $\Omega$

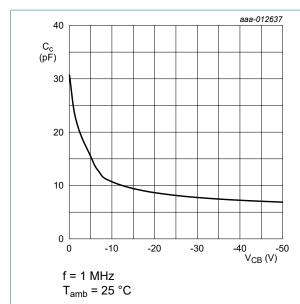


Fig. 15. TR2 (PNP): Collector capacitance as a function of collector-base voltage; typical values

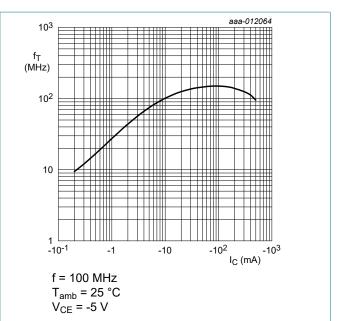


Fig. 16. TR2 (PNP): Transition frequency as a function of collector current; typical values of built-in transistor

50 V, 500 mA NPN/PNP Resistor-Equipped double Transistor (RET); R1 = 2.2 k $\Omega$ , R2 = 10 k $\Omega$ 

## 11. Test information

#### **Resistor calculation**

· Calculation of bias resistor 1 (R1)

$$R1 = \frac{V(I12) - V(I11)}{I12 - I11}$$

· Calculation of bias resistor ratio (R2/R1)

$$\frac{R2}{R1} = \frac{V(I14) - V(I13)}{R1 \cdot (I14 - I13)} - 1$$

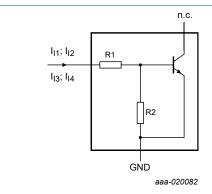


Fig. 17. TR1 (NPN): Resistor test circuit

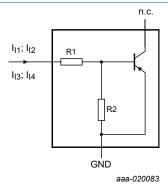


Fig. 18. TR2 (PNP): Resistor test circuit

### **Resistor test conditions**

#### Table 8. Resistor test conditions

Per transistor; for the PNP transistor with negative polarity

R1 (kΩ)	R2 (kΩ)	Test conditions				
		I <sub>11</sub>	I <sub>12</sub>	I <sub>I3</sub>	I <sub>14</sub>	
2.2	10	0.7 mA	0.8 mA	-0.45 mA	-0.55 mA	

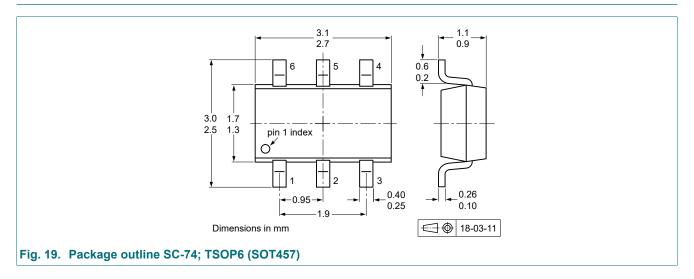
## **Quality information**

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

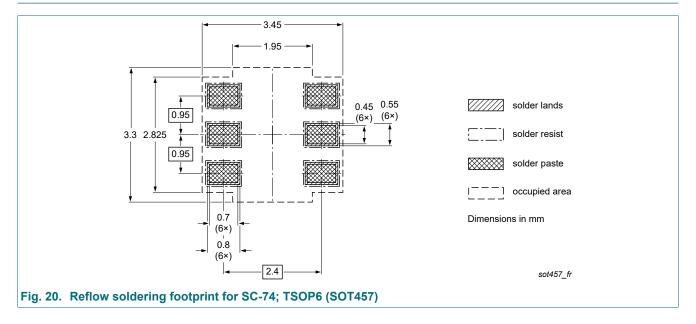
PIMC32-Q

50 V, 500 mA NPN/PNP Resistor-Equipped double Transistor (RET); R1 = 2.2 k $\Omega$ , R2 = 10 k $\Omega$ 

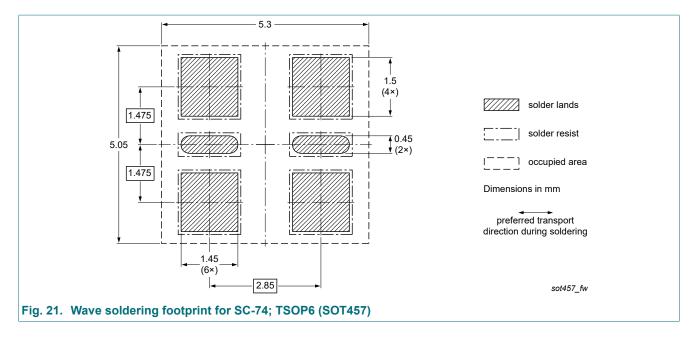
# 12. Package outline



# 13. Soldering



## 50 V, 500 mA NPN/PNP Resistor-Equipped double Transistor (RET); R1 = 2.2 k $\Omega$ , R2 = 10 k $\Omega$



50 V, 500 mA NPN/PNP Resistor-Equipped double Transistor (RET); R1 = 2.2 k $\Omega$ , R2 = 10 k $\Omega$ 

# 14. Revision history

## Table 9. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PIMC32-Q v.1	20220216	Product data sheet	-	-

#### 50 V, 500 mA NPN/PNP Resistor-Equipped double Transistor (RET); R1 = 2.2 k $\Omega$ , R2 = 10 k $\Omega$

# 15. Legal information

#### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
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PIMC32-Q

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For more information, please visit: http://www.nexperia.com For sales office addresses, please send an email to: salesaddresses@nexperia.com Date of release: 16 February 2022

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